

Monolithic CMOS Analog Multiplexers

ABSOLUTE MAXIMUM RATINGS

Voltage Referenced to V-

V+	+44V
GND	+25V
Digital Inputs, Vs and VD (Note 1)	-2V to (V+ + 2V) or 20mA, whichever occurs first
Current (any terminal, except S or D)	30mA
Continuous Current, S or D	20mA
Peak Current, S or D (pulsed at 1ms, 10% duty cycle max)	40mA
Continuous Power Dissipation ($T_A = +70^\circ\text{C}$)	
Plastic DIP (derate 10.53mW/ $^\circ\text{C}$ above $+70^\circ\text{C}$)	842mW
Narrow SO (derate 8.70mW/ $^\circ\text{C}$ above $+70^\circ\text{C}$)	696mW
Wide SO (derate 9.52mW/ $^\circ\text{C}$ above $+70^\circ\text{C}$)	762mW
CERDIP (derate 10.00mW/ $^\circ\text{C}$ above $+70^\circ\text{C}$)	800mW

Note 1: Signals on S_ or D_ exceeding V+ or V- are clamped by internal diodes. Limit forward-diode current to maximum current ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Operating Temperature Ranges:

DG50_ACJ/CWE	0°C to $+70^\circ\text{C}$
DG50_ABK	-20°C to $+85^\circ\text{C}$
DG50_ADJ/DY/EWE	-40°C to $+85^\circ\text{C}$
DG50_AAK/MY	-55°C to $+125^\circ\text{C}$
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Lead Temperature (soldering, 10s)	+300°C
Soldering Temperature (reflow)	
PDIP, Wide SO, Narrow SO, CERDIP containing lead(Pb)	+240°C
PDIP, Wide SO, Narrow SO lead(Pb)-free	+260°C

ELECTRICAL CHARACTERISTICS

($V+ = 15\text{V}$, $V- = -15\text{V}$, $V_{\text{GND}} = 0\text{V}$, $T_A = +25^\circ\text{C}$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	DG508AA/M			DG508AD/E/B/C			UNITS		
			MIN	TYP	MAX	MIN	TYP	MAX			
SWITCH											
Analog Signal		V_{ANALOG}			-15	+15	-15	+15	V		
Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	Sequence each switch on, $V_{\text{A,L}} = 0.8\text{V}$, $V_{\text{A,H}} = 2.4\text{V}$ (Note 4)	$V_D = 10\text{V}$, $I_S = -200\mu\text{A}$	170	400	170	450	Ω			
			$V_D = -10\text{V}$, $I_S = 200\mu\text{A}$	130	400	130	450				
Greatest Change in Drain-Source On-Resistance Between Channels	$\Delta R_{\text{DS(ON)}}$	$\Delta R_{\text{DS(ON)}} = \left(\frac{R_{\text{DS(ON) max}} - R_{\text{DS(ON) min}}}{R_{\text{DS(ON)}}} \right)$ $-10\text{V} \geq V_S \geq 10\text{V}$		6		6		%			
Source Off-Leakage Current	$I_{\text{S(OFF)}}$	$V_{\text{EN}} = 0\text{V}$	$V_S = 10\text{V}, V_D = -10\text{V}$	0.002	0.5	0.002	1	nA			
			$V_S = -10\text{V}, V_D = 10\text{V}$	-0.5	-0.005	-1	-0.005				
Drain Off-Leakage Current	DG508A	$V_{\text{EN}} = 0\text{V}$	$V_D = 10\text{V}, V_S = -10\text{V}$	0.01	2	0.01	5	nA			
			$V_D = -10\text{V}, V_S = 10\text{V}$	-2	-0.015	-5	-0.015				
Drain On-Leakage Current	DG509A	$I_{\text{D(OFF)}}$	$V_D = 10\text{V}, V_S = -10\text{V}$	0.005	2	0.005	5	nA			
			$V_D = -10\text{V}, V_S = 10\text{V}$	-2	-0.008	-5	-0.008				
Drain On-Leakage Current	DG508A	$I_{\text{D(ON)}}$	Sequence each switch on, $V_{\text{A,L}} = 0.8\text{V}$, $V_{\text{A,H}} = 2.4\text{V}$ (Note 2)	$V_{\text{S(all)}} = V_D = 10\text{V}$	0.015	2	0.015	5	nA		
				$V_{\text{S(all)}} = V_D = -10\text{V}$	-2	-0.03	-5	-0.03			
	DG509A			$V_{\text{S(all)}} = V_D = 10\text{V}$	0.007	2	0.007	5			
				$V_{\text{S(all)}} = V_D = -10\text{V}$	-2	-0.015	-5	-0.015			

Monolithic CMOS Analog Multiplexers

ELECTRICAL CHARACTERISTICS (continued)

($V_+ = 15V$, $V_- = -15V$, $V_{GND} = 0V$, $T_A = +25^\circ C$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	DG508AA/M DG509AA/M			DG508AD/E/B/C DG509AD/E/B/C			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
LOGIC INPUT									
Logic Input Current, Input Voltage High	I _{AH}	V _{A_-} = 2.4V	-10	-	10	-0.002			µA
		V _{A_-} = 15V		0.006	10	0.006	10		
Logic Input Current, Input Voltage Low	I _{AL}	All V _{A_-} = 0V	V _{EN} = 2.4V	-10	-	10	-0.002		µA
			V _{EN} = 0V	-10	-	-10	-0.002		
DYNAMIC									
Multiplexer Switching	t _{transition}	Figure 1		0.6	1.0	0.6	1.0		µs
Break-Before-Make Interval	t _{OPEN}	Figure 3		0.2		0.2			µs
Enable Turn-On Time	t _{ON(EN)}	Figure 2		0.4	1.0	0.4	1.5		µs
Enable Turn-Off Time	t _{OFF(EN)}	Figure 2		0.2	0.7	0.2	1.0		µs
Off-Isolation	OIRR	V _{EN} = 0V, R _L = 1kΩ, C _L = 15pF, V _S = 7VRMS f = 500kHz (Note 3)		68		68			dB
Source Off-Capacitance	C _{S(OFF)}	V _S = 0V, V _{EN} = 0V, f = 140kHz		5		5			pF
Drain Off-Capacitance	IDG508A	C _{D(OFF)}	V _S = 0V, V _{EN} = 0V, f = 140kHz	25		25			pF
	DGS09A			12		12			
SUPPLY									
Positive Supply Current	I ₊	V _{EN} = 2.4V, all V _{A_-} = 0V or 2.4V		0.02	0.2	0.02	0.2		mA
Negative Supply Current	I ₋	V _{EN} = 2.4V, all V _{A_-} = 0V or 2.4V	-0.1	-0.01		-0.1	-0.01		mA
Positive Supply Current in Standby	I ₊	V _{EN} = 0V, all V _{A_-} = 0V or 2.4V		0.02	0.2	0.02	0.2		mA
Negative Supply Current in Standby	I ₋	V _{EN} = 0V, all V _{A_-} = 0V or 2.4V	-0.1	-0.01		-0.1	-0.01		mA
Power-Supply Range for Continuous Operation	V ₋ , V ₊	(Notes 4, 5)	±4.5		±18.0	±4.5		±18.0	V

Monolithic CMOS Analog Multiplexers

ELECTRICAL CHARACTERISTICS

(V₊ = 15V, V_{GND} = 0V, T_A = T_{MIN} to T_{MAX}, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	DG508AA/M			DG508AD/E/B/C			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
SWITCH									
Analog Signal Range	V _{ANALOG}		-15	+15	-15	+15			V
Drain-Source On-Resistance	R _{D(S)}	Sequence each switch on, V _{A_L} = 0.8V, V _{A_H} = 2.4V	V _D = 10V, I _S = -200μA	500		550			Ω
			V _D = -10V, I _S = 200μA	500		550			
Source Off-Leakage Current	I _{S(OFF)}	V _{EN} = 0V	V _S = 10V, V _D = -10V		+50		+50		nA
			V _S = -10V, V _D = -10V		-50		-50		
Drain Off-Leakage Current	I _{D(OFF)}	V _{EN} = 0V	V _D = 10V, V _S = -10V		+200		+100		nA
			V _D = -10V, V _S = -10V	-200		-200			
			V _D = 10V, V _S = -10V		+200		+100		
			V _D = -10V, V _S = -10V	-100		-100			
			V _{S(all)} = V _D = 10V		+200		+100		
Drain On-Leakage Current	I _{D(ON)}	Sequence each switch on, V _{A_L} = 0.8V, V _{A_H} = 2.4V (Note 2)	V _{S(all)} = V _D = -10V	-200		-100			nA
			V _{S(all)} = V _D = 10V		+100		+100		
			V _{S(all)} = V _D = -10V	-100		-100			
			V _{S(all)} = V _D = 10V		+100		+100		
LOGIC INPUT									
Logic Input Current, Input Voltage High	I _{AH}	V _{A_} = 2.4V V _{A_} = 15V		-30		-30		+30	μA
					+30			+30	
Logic Input Current, Input Voltage Low	I _{AL}	All V _{A_} = 0V	V _{EN} = 2.4V	-30		-30			μA
			V _{EN} = 0V	-30		-30			

Note 2: I_{D(ON)} is leakage from driver into on switch.

$$\text{Note 3: Off-isolation} = 20 \log \frac{|V_S|}{|V_D|}$$

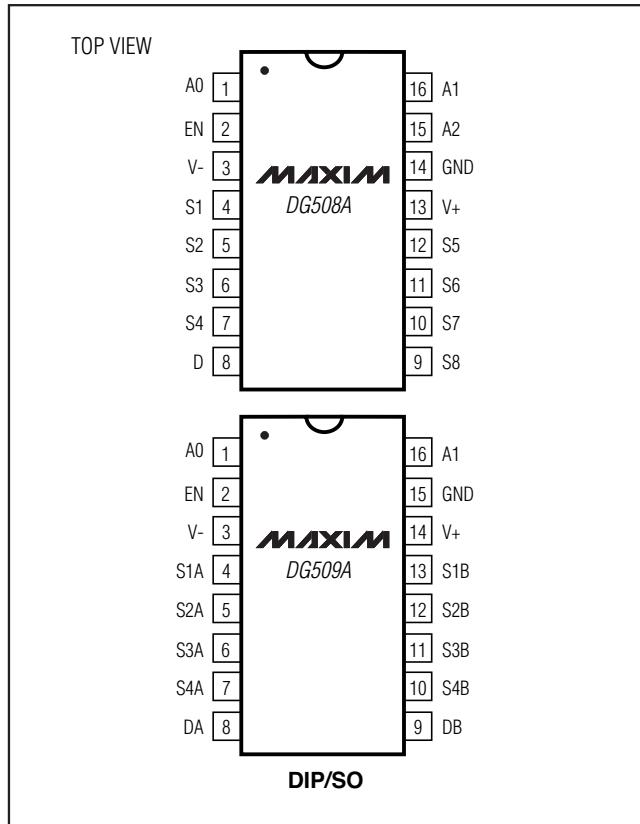
V_S = input to off switch,
V_D = output due to V_S.

Note 4: Electrical characteristics (such as on-resistance) change when power supplies other than ±15V are used.

Note 5: For designs requiring single 5V or dual ±5V operation, refer to Maxim's improved MAX338 and MAX339. Minimum operating voltage for DG508ADY/MY and DG509ADY/MY is ±9V.

Monolithic CMOS Analog Multiplexers

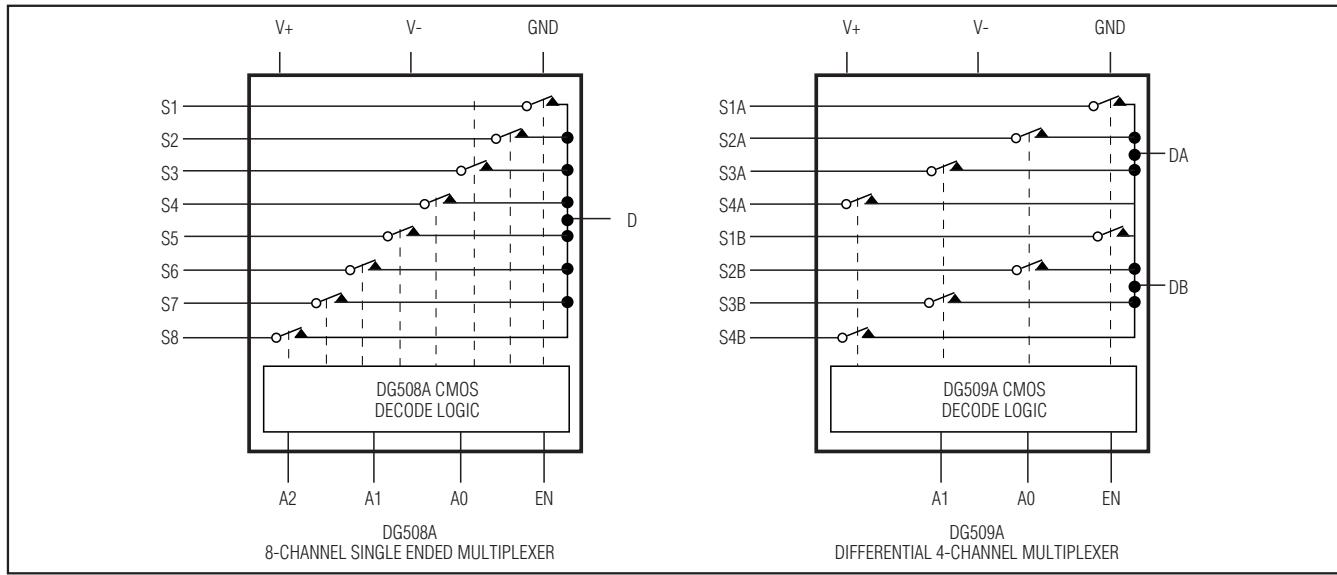
Pin Configurations



Pin Descriptions

PIN		NAME	FUNCTION
DG508A	DG509A		
1, 15, 16	—	A0, A2, A1	Address Input
—	1, 16	A0, A1	Address Input
2	2	EN	Enable
3	3	V-	Negative-Supply Voltage Input
4–7	—	S1–S4	Analog Inputs, Bidirectional
—	4–7	S1A–S4A	Analog Inputs, Bidirectional
8	—	D	Analog Outputs, Bidirectional
—	8, 9	DA, DB	Analog Outputs, Bidirectional
9–12	—	S8–S5	Analog Inputs, Bidirectional
—	10–13	S4B–S1B	Analog Inputs, Bidirectional
13	14	V+	Positive-Supply Voltage Input
14	15	GND	Ground

Functional Diagrams



DG508A/DG509A

Monolithic CMOS Analog Multiplexers

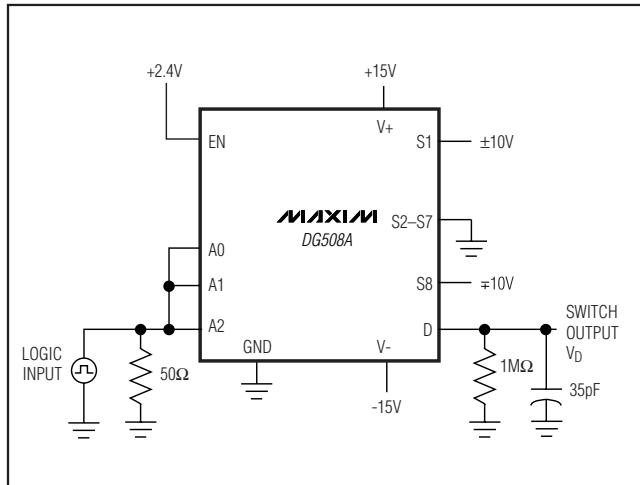


Figure 1a. Switching-Time Test Circuit

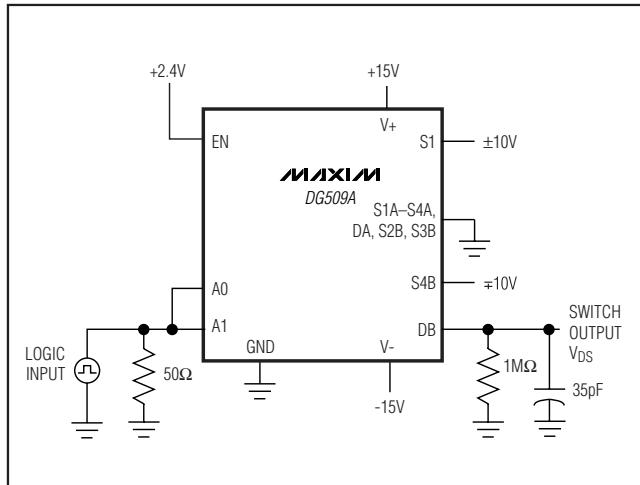


Figure 1b. Switching-Time Test Circuit

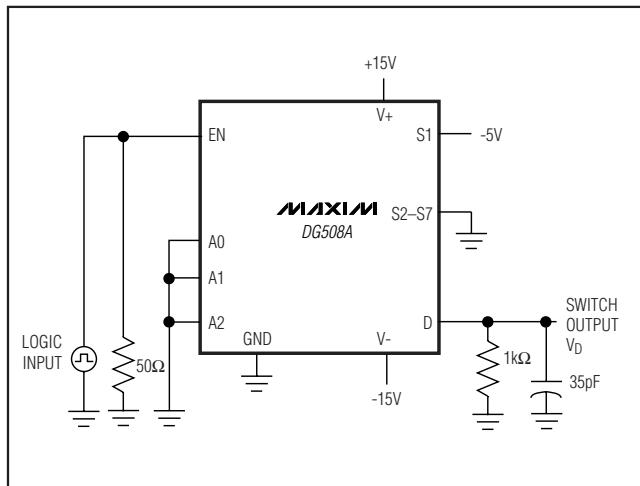


Figure 2a. DG508A Enable-Time Test Circuit

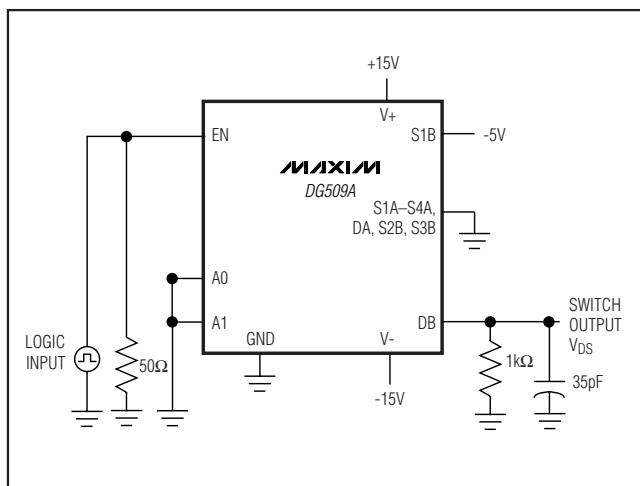


Figure 2b. DG509A Enable-Time Test Circuit

Monolithic CMOS Analog Multiplexers

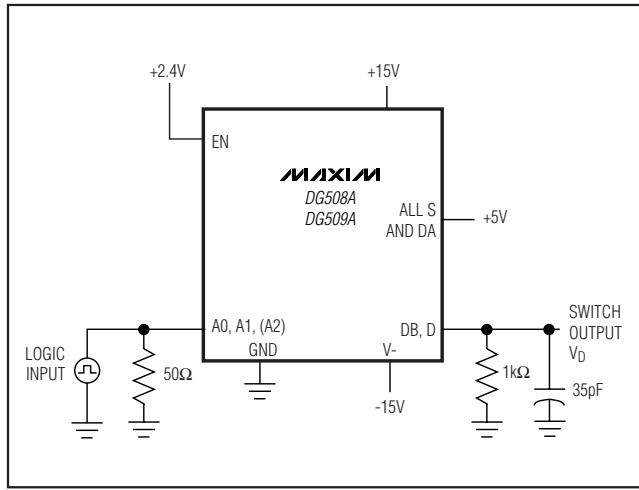


Figure 3. Break-Before-Make Test Circuit

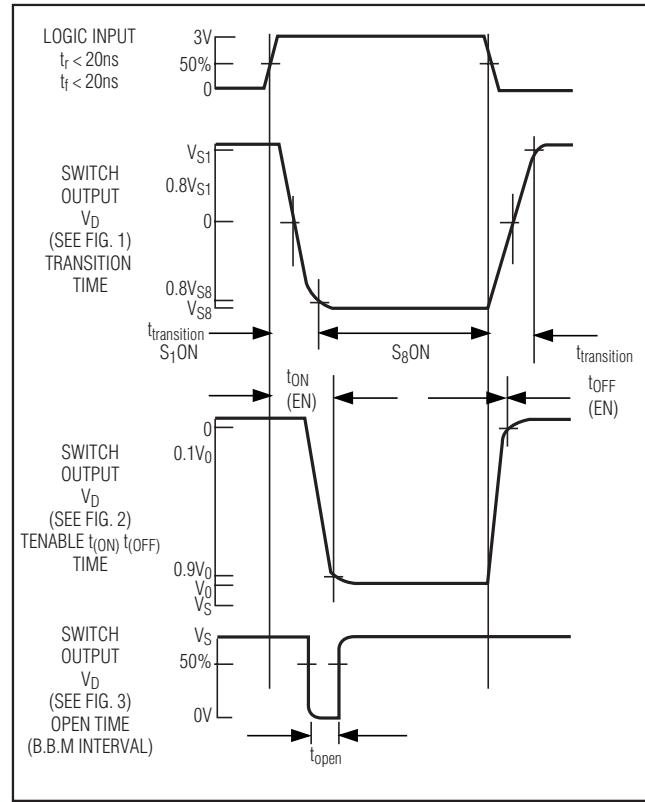


Figure 4. Timing Diagram for Figures 1, 2, and 3

Table 1a. DG508A Truth Table

A2	A1	A0	EN	ON SWITCH
X	X	X	0	NONE
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

X = Don't care.

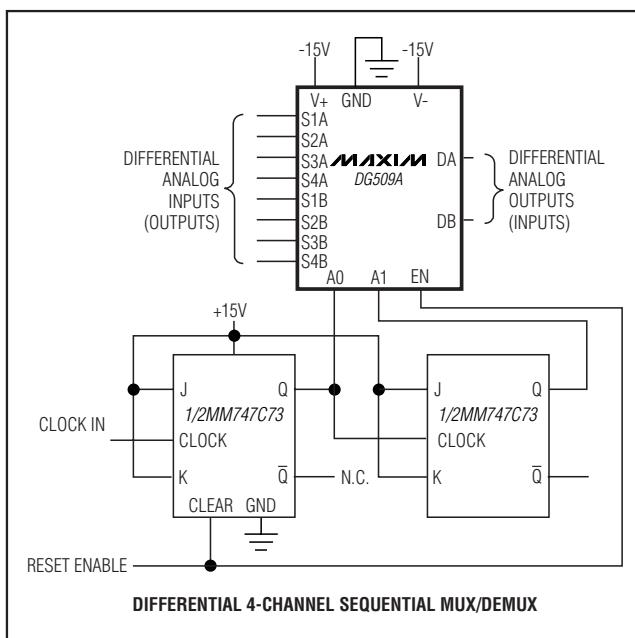
Table 1b. DG509A Truth Table

A1	A0	EN	ON SWITCH
X	X	0	NONE
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

X = Don't care.

Monolithic CMOS Analog Multiplexers

Typical Operating Circuits (continued)



Package Information

For the latest package outline information and land patterns, go to www.maxim-ic.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
16 Plastic DIP	P16-1	21-0043
16 Wide SO	W16-2	21-0042
16 Narrow SO	S16-5	21-0041
16 Cerdip	J16-3	21-0045

Monolithic CMOS Analog Multiplexers

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
4	5/10	Updated the “Drain-Source On-Resistance” parameter for both the TA = +25°C and TA = TMIN to TMAX conditions.	2, 4
		Deleted the QFN package from the <i>Ordering Information</i> , <i>Absolute Maximum Ratings</i> , <i>Pin Configurations</i> , <i>Pin Descriptions</i> , and <i>Package Information</i> sections.	1, 2, 5, 8
		Added the DG508AMY/PR and DG509AMY/PR parts to the <i>Ordering Information</i> table.	1

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

Maxim Integrated Products, 120 San Gabriel Drive, Sunnyvale, CA 94086 408-737-7600 _____ 9

© 2010 Maxim Integrated Products

Maxim is a registered trademark of Maxim Integrated Products, Inc.